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HYBRID BONDING AND METHOD FOR
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A semiconductor structure includes a first device assembly and a second device assembly. Each of the first and second device assembly includes a substrate, a main unit disposed on the substrate and including at least one device, a dielectric unit disposed on the main unit and having an interconnecting surface opposite to the substrate, and an electrically conductive routing disposed in the dielectric unit, electrically connected to the at least one device, and including an end portion. The interconnecting surface of the dielectric unit of the first device assembly is bonded to the interconnecting surface of the dielectric unit of the second device assembly such that the end portion of the electrically conductive routing of the first device assembly is in direct contact with the end portion of the electrically conductive routing of the second device assembly. A method for manufacturing the semiconductor structure are also disclosed.

